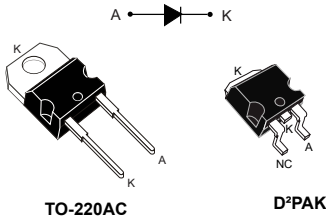


## 650 V power Schottky silicon carbide diode



### Features

- No or negligible reverse recovery
- Switching behavior independent of temperature
- Dedicated to PFC applications
- High forward surge capability
- Operating  $T_j$  from  $-40\text{ }^\circ\text{C}$  to  $175\text{ }^\circ\text{C}$
- ECOPACK<sup>®</sup> 2 compliant
- Power efficient product

### Applications

- DC/DC converter
- High frequency inverter
- Snubber
- Boost PFC function

### Description

The SiC diode is an ultra high performance power Schottky diode. It is manufactured using a silicon carbide substrate. The wide band gap material allows the design of a Schottky diode structure with a 650 V rating. Due to the Schottky construction, no recovery is shown at turn-off and ringing patterns are negligible. The minimal capacitive turn-off behavior is independent of temperature.

Especially suited for use in PFC applications, this ST SiC diode will boost performance in hard switching conditions. Its high forward surge capability ensures good robustness during transient phases.

Product status link	
<a href="#">STPSC12065</a>	
Product summary	
Symbol	Value
$I_{F(AV)}$	12 A
$V_{RRM}$	650 V
$T_j$ (max.)	$175\text{ }^\circ\text{C}$
$V_F$ (typ.)	1.30 V

# 1 Characteristics

**Table 1. Absolute ratings (limiting values at 25 °C, unless otherwise specified)**

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	650	V
$I_{F(RMS)}$	Forward rms current	22	A
$I_{F(AV)}$	Average forward current	$T_C = 145\text{ °C}$ , DC <sup>(1)</sup>	A
$I_{FRM}$	Repetitive peak forward current	$T_C = 145\text{ °C}$ , $T_J = 175\text{ °C}$ , $\delta = 0.1$	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal, $T_C = 25\text{ °C}$	50
		$t_p = 10\text{ ms}$ sinusoidal, $T_C = 125\text{ °C}$	40
		$t_p = 10\text{ }\mu\text{s}$ square, $T_C = 25\text{ °C}$	220
$T_{stg}$	Storage temperature range	-55 to +175	°C
$T_J$	Operating junction temperature <sup>(2)</sup>	-40 to +175	°C

1. Value based on  $R_{th(j-c)}$  max.

2.  $(dP_{tot}/dT_J) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

**Table 2. Thermal resistance parameters**

Symbol	Parameter	Value		Unit
		Typ.	Max.	
$R_{th(j-c)}$	Junction to case	0.85	1.25	°C/W

**Table 3. Static electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_R$ <sup>(1)</sup>	Reverse leakage current	$T_J = 25\text{ °C}$	-	15	150	$\mu\text{A}$
		$T_J = 150\text{ °C}$		200	1000	
		$T_J = 25\text{ °C}$	600 V	8	50	
$V_F$ <sup>(2)</sup>	Forward voltage drop	$T_J = 25\text{ °C}$	-	1.30	1.45	V
		$T_J = 150\text{ °C}$		1.45	1.65	
		$T_J = 175\text{ °C}$		1.50		

1. Pulse test:  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

2. Pulse test:  $t_p = 500\text{ }\mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.02 \times I_{F(AV)} + 0.065 \times I_{F(RMS)}^2$$

**Table 4. Dynamic electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$Q_{Cj}$ <sup>(1)</sup>	Total capacitive charge	$V_R = 400\text{ V}$	-	36	-	nC

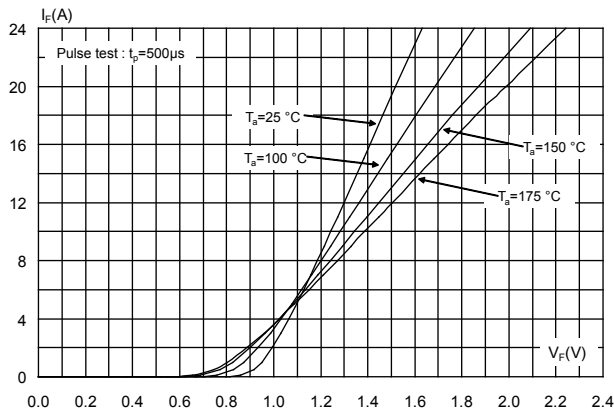
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_j$	Total capacitance	$V_R = 0 \text{ V}, T_C = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	-	750	-	pF
		$V_R = 400 \text{ V}, T_C = 25 \text{ }^\circ\text{C}, F = 1 \text{ MHz}$	-	60	-	

1. Most accurate value for the capacitive charge:

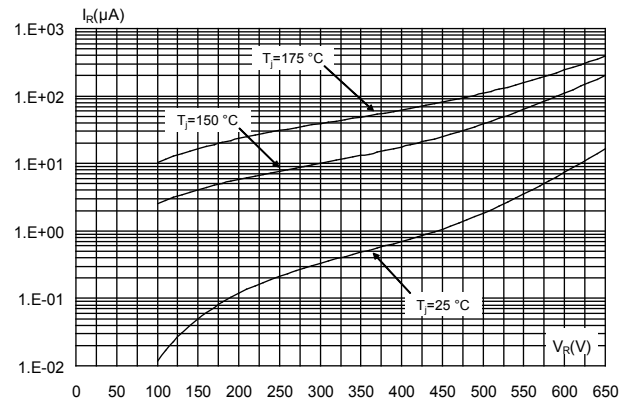
$$Q_{cj} = \int_0^{V_{OUT}} C_j(V_R) \cdot dV_R \quad (1)$$

## 1.1 Characteristics (curves)

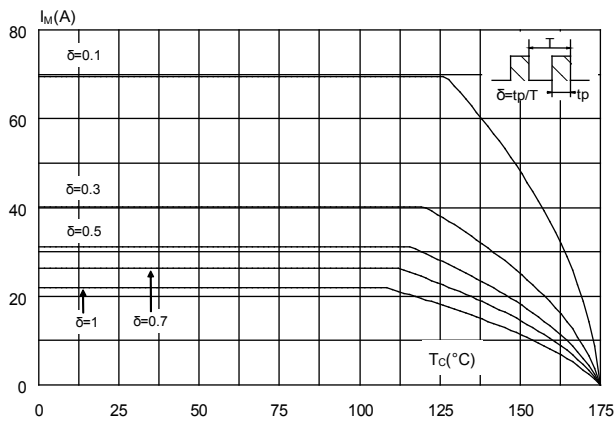
**Figure 1. Forward voltage drop versus forward current (typical values)**



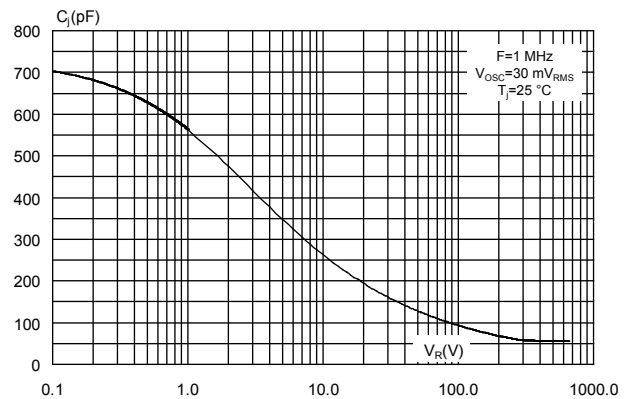
**Figure 2. Reverse leakage current versus reverse voltage applied (typical values)**



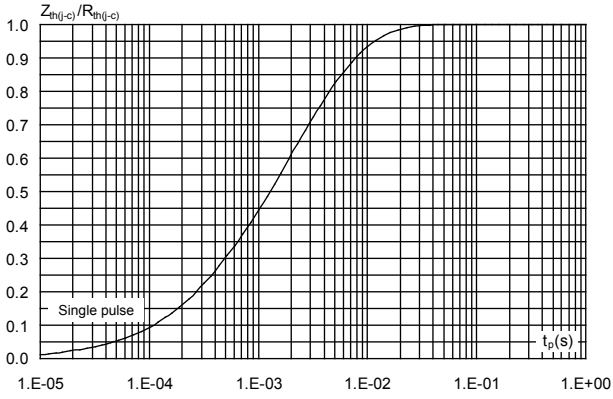
**Figure 3. Peak forward current versus case temperature**



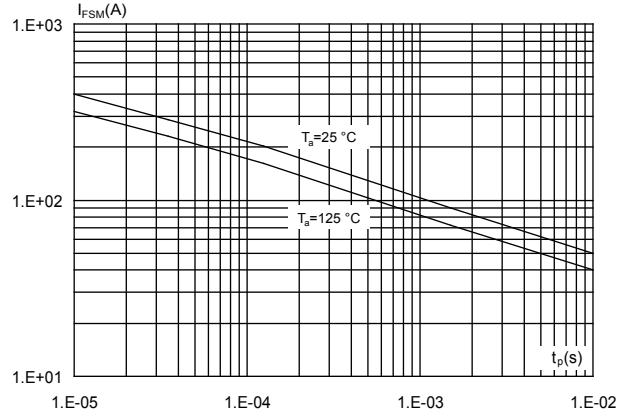
**Figure 4. Junction capacitance versus reverse voltage applied (typical values)**



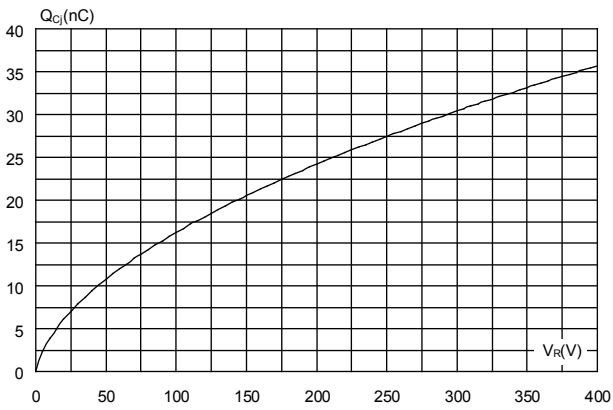
**Figure 5. Relative variation of thermal impedance junction to case versus pulse duration**



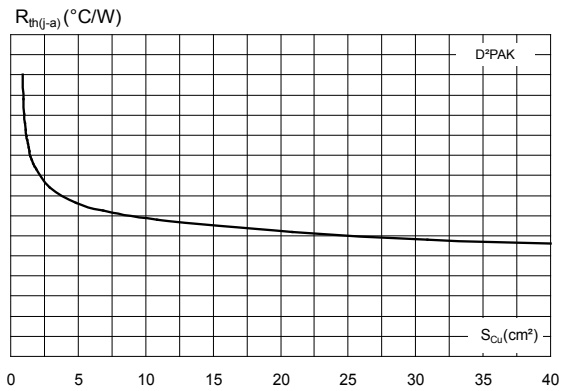
**Figure 6. Non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)**



**Figure 7. Total capacitive charges versus reverse voltage applied (typical values)**



**Figure 8. Thermal resistance junction to ambient versus copper surface under tab (typical values, epoxy printed board FR4,  $e_{Cu} = 35 \mu\text{m}$ )**



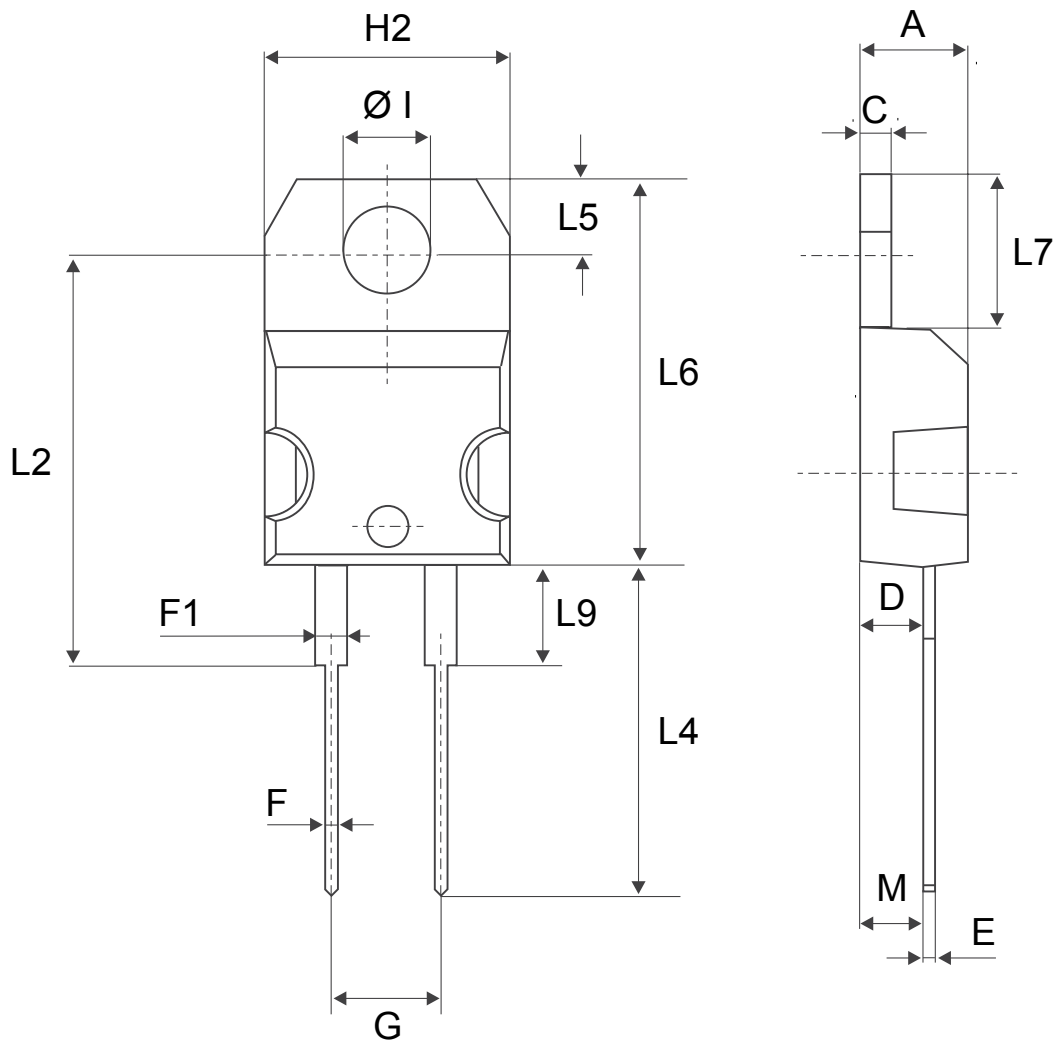
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 2.1 TO-220AC package information

- Epoxy meets UL 94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 9. TO-220AC package outline



**Table 5. TO-220AC package mechanical data**

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
ØI	3.75	3.85	0.147	0.151

## 2.2 D<sup>2</sup>PAK package information

- Epoxy meets UL94, V0.
- Cooling method: by conduction (C)

Figure 10. D<sup>2</sup>PAK package outline

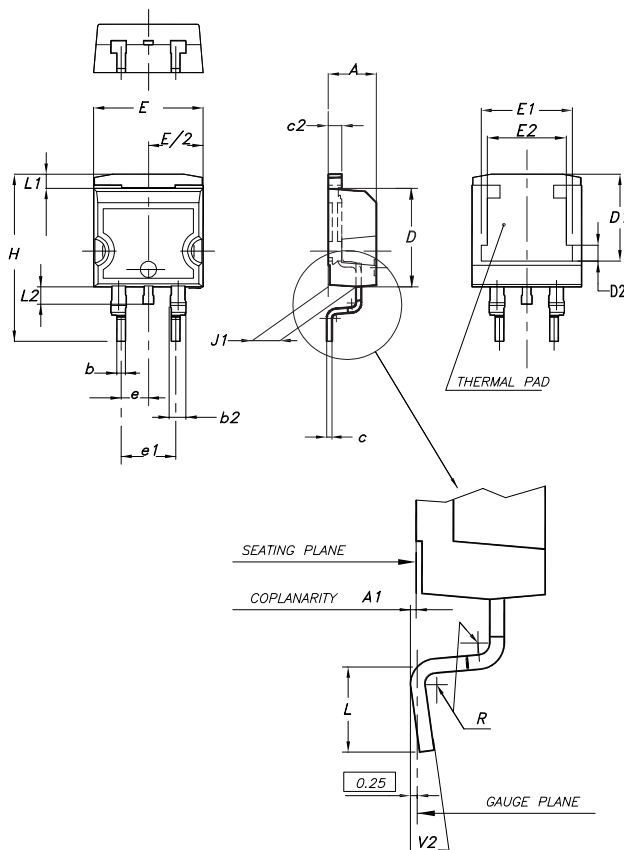
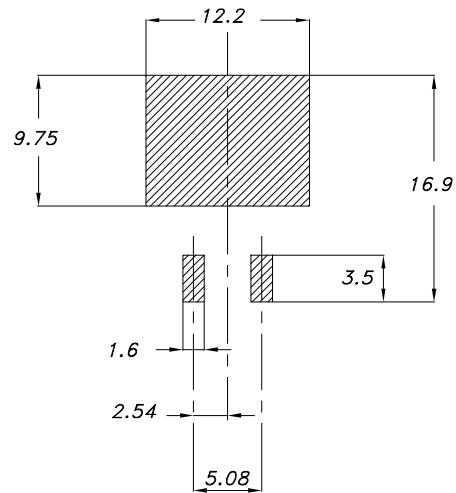


Table 6. D<sup>2</sup>PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10		10.40	0.394		0.409
E1	8.50	8.70	8.90	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.4			0.015	
V2	0°		8°	0°		8°

**Figure 11. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)**



Footprint



### 3 Ordering information

**Table 7. Ordering information**

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPSC12065D	PSC12065D	TO-220AC	1.86 g	50	Tube
STPSC12065G-TR	PSC12065G	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel

## Revision history

**Table 8. Document revision history**

Date	Revision	Changes
29-Apr-2016	1	First issue.
12-Jul-2018	2	Added D <sup>2</sup> PAK package and Applications section.

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